BC847CDXV6T1G, SBC847CDXV6T1G, BC847CDXV6T5G, BC848CDXV6T1G

Dual General Purpose Transistors

NPN Duals

These transistors are designed for general purpose amplifier applications. They are housed in the SOT-563 which is designed for low power surface mount applications.

Features

- AEC-Q101 Qualified and PPAP Capable
- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements
- These are Pb-Free Devices

MAXIMUM RATINGS

Rating	Symbol	BC847	BC848	Unit
Collector - Emitter Voltage	V_{CEO}	45	30	V
Collector - Base Voltage	V _{CBO}	50	30	V
Emitter - Base Voltage	V _{EBO}	6.0	5.0	V
Collector Current - Continuous	Ic	100	100	mAdc

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

THERMAL CHARACTERISTICS

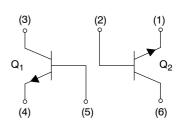
Characteristic (One Junction Heated)	Symbol	Max	Unit
Total Device Dissipation, (Note 1) T _A = 25°C Derate above 25°C	P _D	357 2.9	mW mW/°C
Thermal Resistance, Junction-to-Ambient (Note 1)	$R_{\theta JA}$	350	°C/W
Characteristic			
(Both Junctions Heated)	Symbol	Max	Unit
Total Device Dissipation, (Note 1) T _A = 25°C Derate above 25°C	Symbol P _D	Max 500 4.0	mW mW/°C
Total Device Dissipation, (Note 1) $T_A = 25^{\circ}C$		500	mW

^{1.} FR-4 @ Minimum Pad



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BC847CDXV6T1



SOT-563 CASE 463A

MARKING DIAGRAMS



1x = Device Code

x = G or M M = Date Code

= Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

BC847CDXV6T1G, SBC847CDXV6T1G, BC847CDXV6T5G, BC848CDXV6T1G

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS					
Collector – Emitter Breakdown Voltage (I _C = 10 mA) BC847CDXV6T1, SBC847CDXV6 BC848CDXV6T1	V _(BR) CEO	45 30	_ _	- -	V
Collector – Emitter Breakdown Voltage (I _C = 10 μA, V _{EB} = 0) BC847CDXV6T1, SBC847CDXV6 BC848CDXV6T1	V _{(BR)CES}	50 30	_ _	- -	V
Collector – Base Breakdown Voltage (I _C = 10 μA) BC847CDXV6T1, SBC847CDXV6 BC848CDXV6T1	V _{(BR)CBO}	50 30	_ _	- -	V
Emitter – Base Breakdown Voltage (I _E = 1.0 μA) BC847CDXV6T1, SBC847CDXV6 BC848CDXV6T1	V _{(BR)EBO}	6.0 5.0	_ _	- -	V
Collector Cutoff Current (V _{CB} = 30 V) $(V_{CB} = 30 \text{ V}, T_{A} = 150^{\circ}\text{C})$	I _{CBO}		- -	15 5.0	nA μA
ON CHARACTERISTICS	•				
DC Current Gain (I _C = 10 μ A, V _{CE} = 5.0 V) (I _C = 2.0 mA, V _{CE} = 5.0 V)	h _{FE}	- 420	270 520	- 800	-
Collector – Emitter Saturation Voltage (I_C = 10 mA, I_B = 0.5 mA) (I_C = 100 mA, I_B = 5.0 mA)	V _{CE(sat)}		- -	0.25 0.6	V
Base – Emitter Saturation Voltage (I_C = 10 mA, I_B = 0.5 mA) (I_C = 100 mA, I_B = 5.0 mA)	V _{BE(sat)}		0.7 0.9	- -	V
Base – Emitter Voltage (I_C = 2.0 mA, V_{CE} = 5.0 V) (I_C = 10 mA, V_{CE} = 5.0 V)	V _{BE(on)}	580 -	660 -	700 770	mV
SMALL-SIGNAL CHARACTERISTICS					
Current – Gain – Bandwidth Product ($I_C = 10 \text{ mA}, V_{CE} = 5.0 \text{ Vdc}, f = 100 \text{ MHz}$)	f _T	100	-	-	MHz
Output Capacitance (V _{CB} = 10 V, f = 1.0 MHz)	C _{obo}	_	-	1.5	pF
Noise Figure (I _C = 0.2 mA, V _{CE} = 5.0 Vdc, R _S = 2.0 k Ω ,f = 1.0 kHz, BW = 200 Hz)	NF	_	-	10	dB

ORDERING INFORMATION

Device	Specific Marking	Package	Shipping [†]
BC847CDXV6T1G			4000 Units / Tape & Reel
SBC847CDXV6T1G	1G	SOT-563 (Pb-Free)	
BC847CDXV6T5G		,	8000 Units / Tape & Reel
BC848CDXV6T1G	1L	SOT-563 (Pb-Free)	4000 Units / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

BC847CDXV6T1G, SBC847CDXV6T1G, BC847CDXV6T5G, BC848CDXV6T1G

TYPICAL CHARACTERISTICS

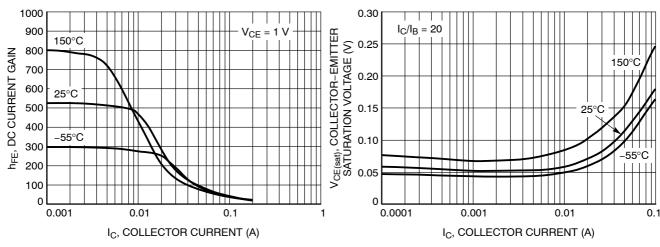


Figure 1. DC Current Gain vs. Collector Current

Figure 2. Collector Emitter Saturation Voltage vs. Collector Current

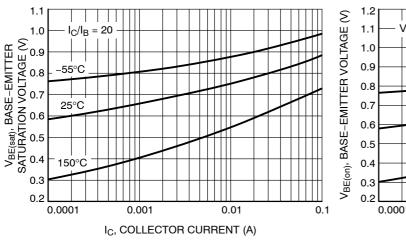


Figure 3. Base Emitter Saturation Voltage vs.
Collector Current

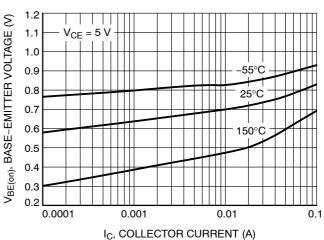


Figure 4. Base Emitter Voltage vs. Collector Current

BC847CDXV6T1G, SBC847CDXV6T1G, BC847CDXV6T5G, BC848CDXV6T1G

TYPICAL CHARACTERISTICS

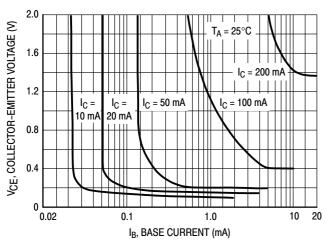
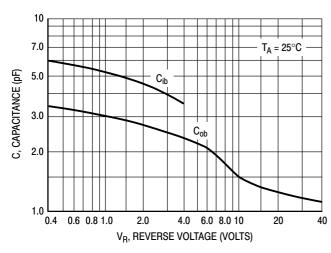


Figure 5. Collector Saturation Region

Figure 6. Base-Emitter Temperature Coefficient



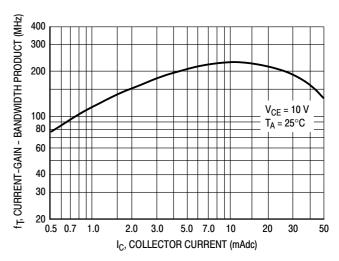


Figure 7. Capacitances

Figure 8. Current-Gain - Bandwidth Product

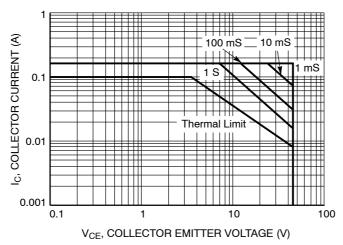


Figure 9. Safe Operating Area



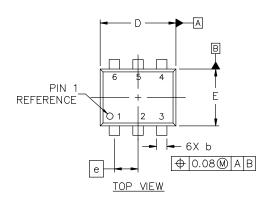


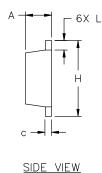
SOT-563-6 1.60x1.20x0.55, 0.50P CASE 463A **ISSUE J**

DATE 15 FEB 2024

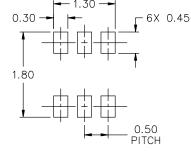
NOTES:

- DIMENSIONING AND TOLERANCING CONFORM TO ASME Y14.5-2018.
- ALL DIMENSION ARE IN MILLIMETERS.
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.





DIM	MILLIMETERS		
ואונע	MIN.	N□M.	MAX.
Α	0.50	0.55	0.60
b	0.17	0.22	0.27
C	0.08	0.13	0.18
D	1.50	1.60	1.70
E	1.10	1.20	1.30
е	0.50 BSC		
Н	1.50	1.60	1.70
L	0.10	0.20	0.30



STYLE 1:	STYLE 2:	STYLE 3:
PIN 1. EMITTER 1	PIN 1. EMITTER 1	PIN 1. CATHODE 1
2. BASE 1	2. EMITTER 2	2. CATHODE 1
3. COLLECTOR 2	3. BASE 2	3. ANODE/ANODE 2
4. EMITTER 2	4. COLLECTOR 2	4. CATHODE 2
5. BASE 2	5. BASE 1	5. CATHODE 2
6. COLLECTOR 1	6. COLLECTOR 1	6. ANODE/ANODE 1

STYLE 6: PIN 1. CATHODE 2. ANODE

3. CATHODE

4. CATHODE 5. CATHODE

CATHODE

RECOMMENDED	MOLINITING	FOOTDRINIT*
KECOMIMENDED	MOONTING	LOO INKINI.

FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

STYLE 7:	STYLE 8:	STYLE 9:
PIN 1. CATHODE	PIN 1. DRAIN	PIN 1. SOURCE 1
2. ANODE	2. DRAIN	2. GATE 1
3. CATHODE	3. GATE	3. DRAIN 2
4. CATHODE	4. SUURCE	4. SOURCE 2
5. ANODE	5. DRAIN	5. GATE 2
6. CATHODE	6. DRAIN	6. DRAIN 1

STYLE 5

PIN 1. CATHODE

2. CATHODE 3. ANDDE 4. ANDDE 5. CATHODE

GENERIC MARKING DIAGRAM*



XX = Specific Device Code M = Month Code

= Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "=", may or may not be present. Some products may not follow the Generic Marking.

PIN 1. CATHODE 1	PIN 1. EMITTER 2
2. N/C	2. BASE 2
3. CATHODE 2	3. COLLECTOR 1
4. ANODE 2	4. EMITTER 1
5. N/C	5. BASE 1
6. AN□DE 1	6. COLLECTOR 2

STYLE 11:

STYLE 4: PIN 1. COLLECTOR

3. BASE 4. EMITTER 5. COLLECTOR

STYLE 10:

2. COLLECTOR

COLLECTOR

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DESCRIPTION: SOT-563-6 1.60x1.20x0.55, 0.50P **PAGE 1 OF 1**

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